Ordering number : ENA1712A

ATP214

N-Channel Power MOSFET
60V, 75A, 8.1mΩ, Single ATPAK

ON Semiconductor®
http://onsemi.com

Features

- ON-resistance $R_{DS}(on)1$=6.2mΩ(typ.)
- 4V drive
- Protection diode in
- Input Capacitance Ciss=4850pF(typ.)
- Halogen free compliance

Specifications

Absolute Maximum Ratings at Ta=25°C

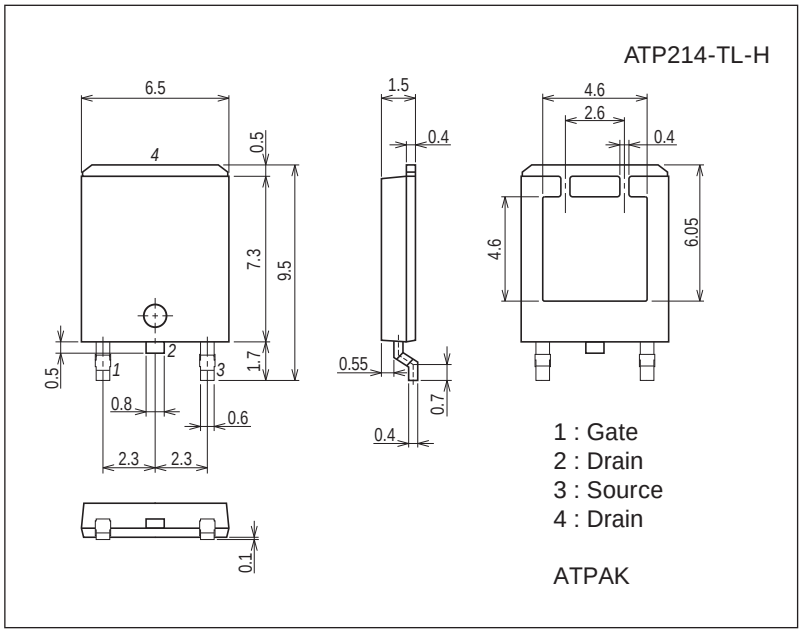
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		60	V
Gate-to-Source Voltage	V_{GSS}		±20	V
Drain Current (DC)	I_D		75	A
Drain Current (PW≤10μs)	I_{DP}	PW≤10μs, duty cycle≤1%	225	A
Allowable Power Dissipation	P_D	Tc=25°C	60	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C
Avalanche Energy (Single Pulse) *1	E_{AS}		94	mJ
Avalanche Current *2	I_{AV}		38	A

Note :*1 V_{DD}=15V, L=100μH, I_{AV}=38A
*2 L≤100μH, Single pulse

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

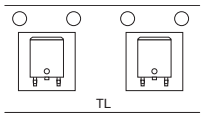
unit : mm (typ)
7057-001



Product & Package Information

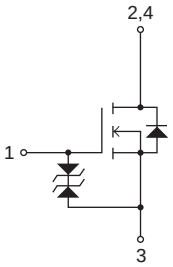
- Package : ATPAK
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

Packing Type: TL



Marking

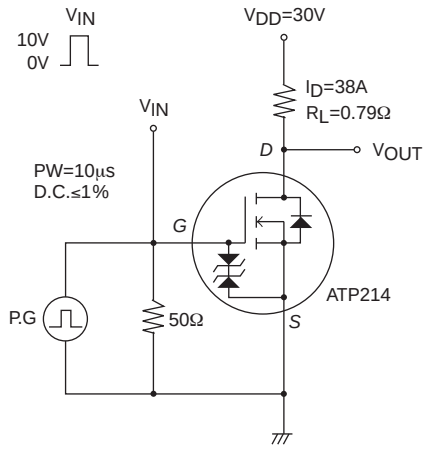
Electrical Connection



Electrical Characteristics at Ta=25°C

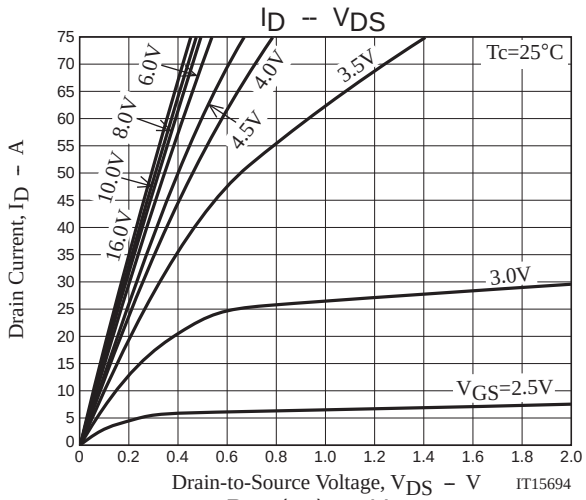
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0V	60			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V, V_{GS}=0V			1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±16V, V_{DS}=0V			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}=10V, I_D=1mA	1.2		2.6	V
Forward Transfer Admittance	| yfs |	V_{DS}=10V, I_D=38A		100		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D=38A, V_{GS}=10V		6.2	8.1	mΩ
	R_{DS}(on)2	I_D=19A, V_{GS}=4.5V		8.2	11.5	mΩ
	R_{DS}(on)3	I_D=10A, V_{GS}=4V		9.2	14	mΩ
Input Capacitance	Ciss	V_{DS}=20V, f=1MHz		4850		pF
Output Capacitance	Coss			370		pF
Reverse Transfer Capacitance	Crss			280		pF
Turn-ON Delay Time	t_d(on)	See specified Test Circuit.		30		ns
Rise Time	t_r			240		ns
Turn-OFF Delay Time	t_d(off)			360		ns
Fall Time	t_f			250		ns
Total Gate Charge	Qg	V_{DS}=30V, V_{GS}=10V, I_D=75A		96		nC
Gate-to-Source Charge	Qgs			18.5		nC
Gate-to-Drain “Miller” Charge	Qgd			18		nC
Diode Forward Voltage	V_{SD}	I_S=75A, V_{GS}=0V		0.93	1.2	V

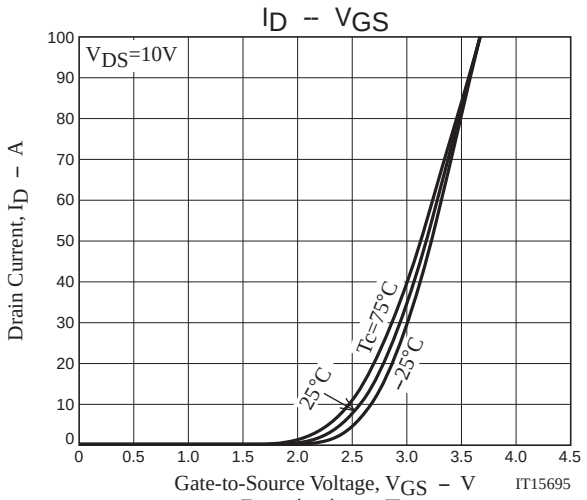
Switching Time Test Circuit

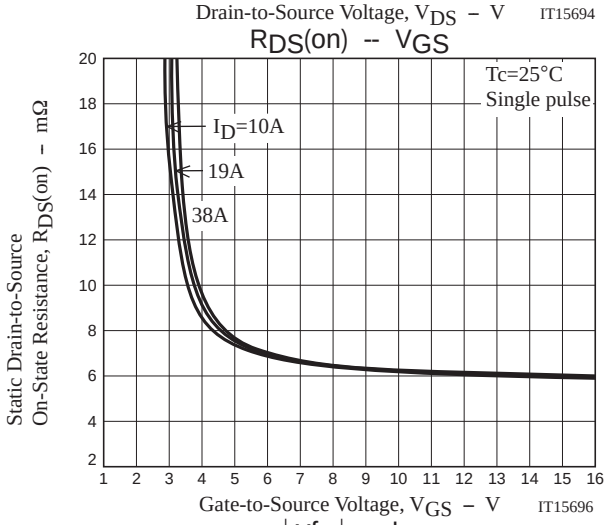


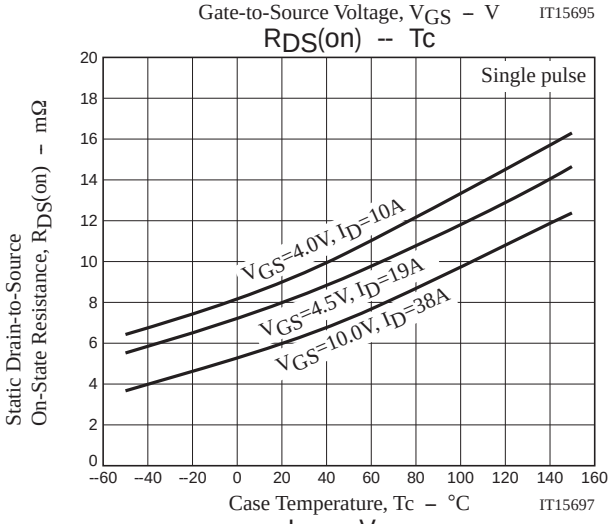
Ordering Information

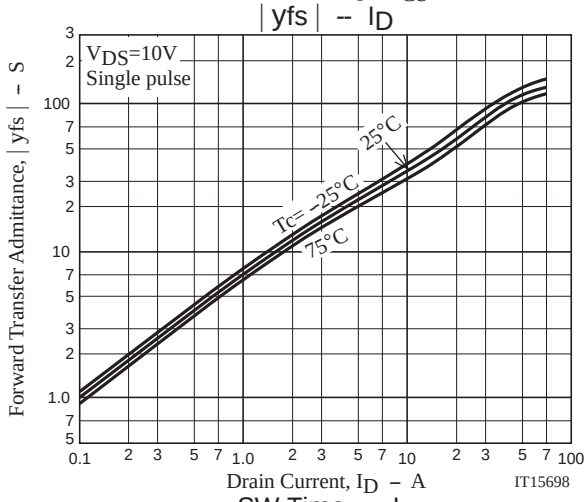
Device	Package	Shipping	memo
ATP214-TL-H	ATPAK	3,000pcs./reel	Pb Free and Halogen Free

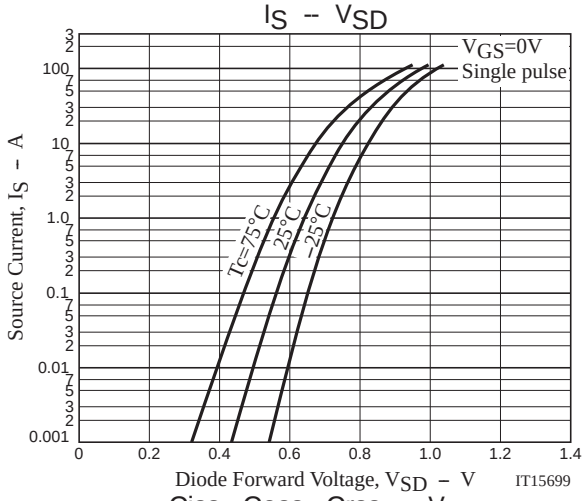


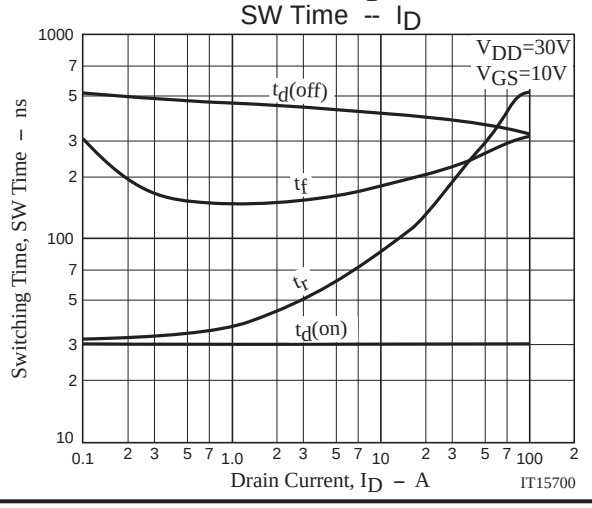


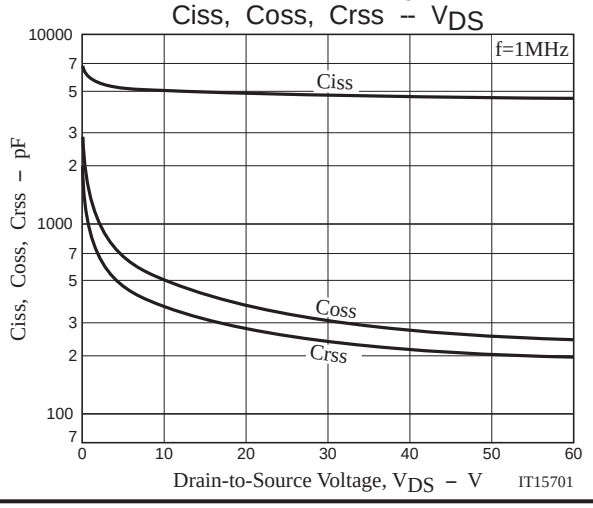


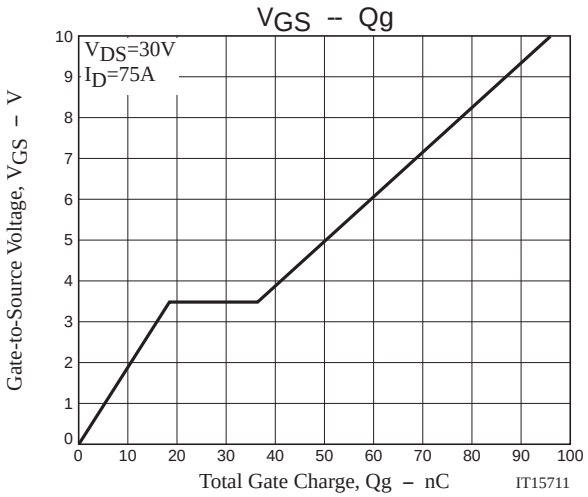


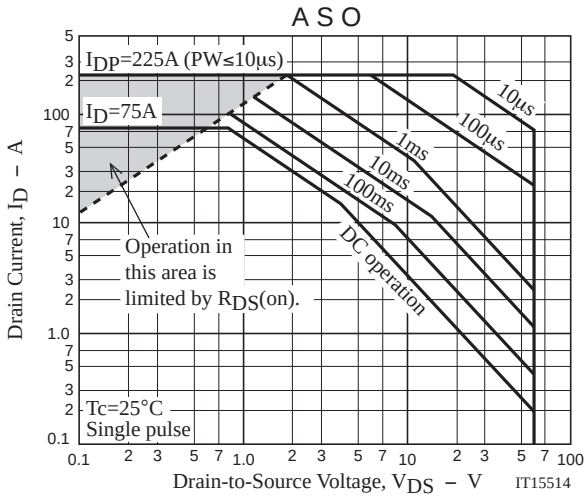


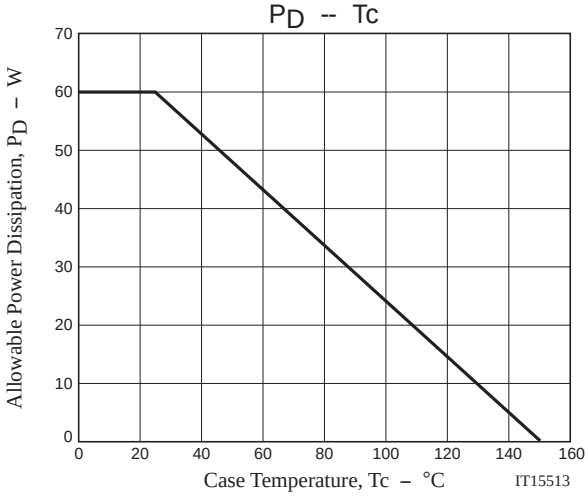


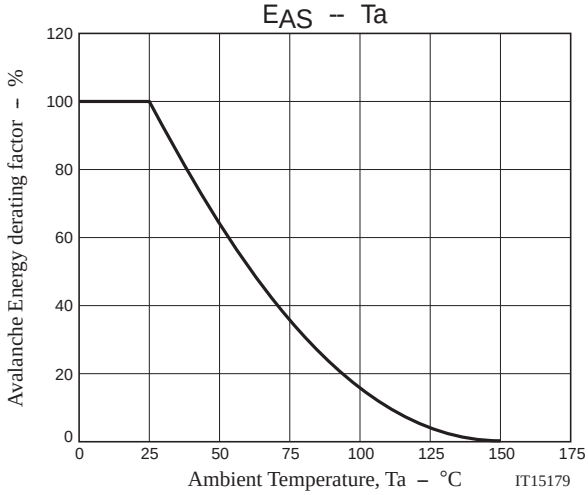












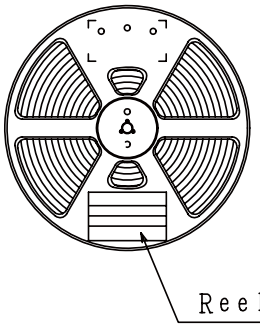
Taping Specification

ATP214-TL-H

1. Packing Format (TL)

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	INNER BOX SD-C-18	OUTER BOX SD-A-18
ATPAK	ATP	3,000	3,000	15,000	1 reels contained Dimensions:mm (external) 340×340×28	5 inner boxes contained Dimensions:mm (external) 355×355×165

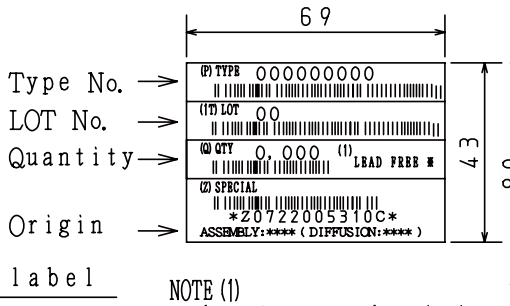
Packing method



Reel label

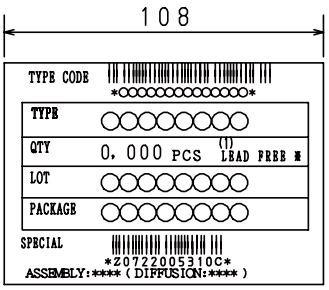
Reel label, Inner box label

(unit:mm)



Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



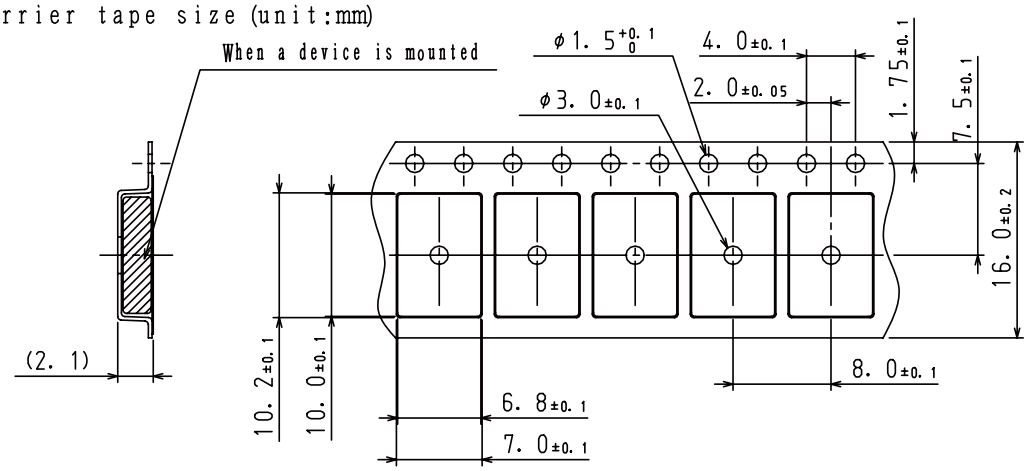
NOTE (1)

The LEAD FREE ※ description shows that the surface treatment of the terminal is lead free.

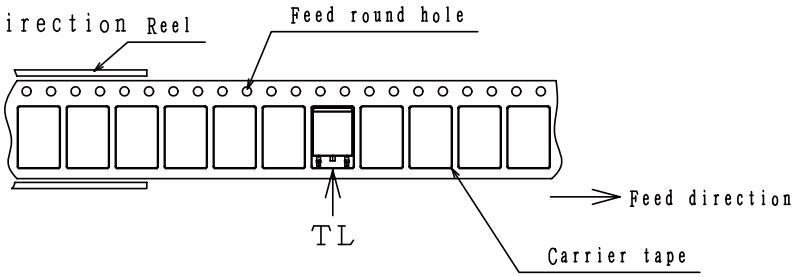
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



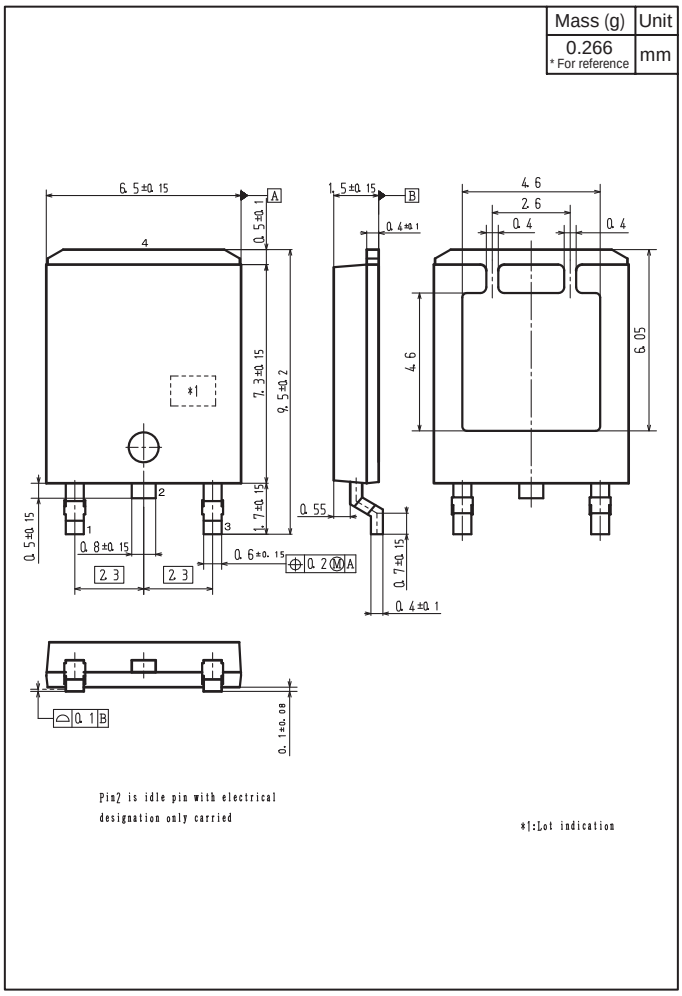
2-2. Device placement direction



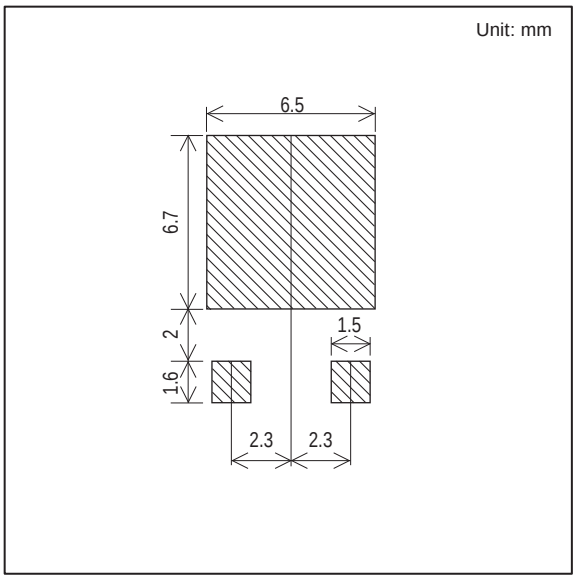
The one erectrode terminals on feed hole side····TL

Outline Drawing

ATP214-TL-H



Land Pattern Example



Note on usage : Since the ATP214 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.